



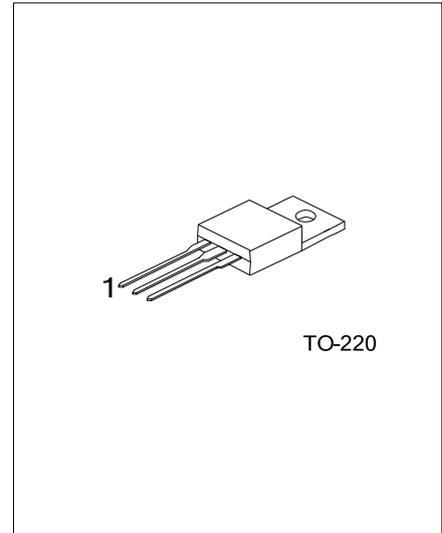
2SA940

PNP SILICON TRANSISTOR

PNP SILICON POWER TRANSISTORS

FEATURES

- * Collector-Emitter Voltage: $V_{CE0} = -150V$ (Min.)
- * DC Current Gain: $h_{FE} = 40 \sim 140$ @ $I_C = -500mA$
- * Complementary of NPN 2SC2073



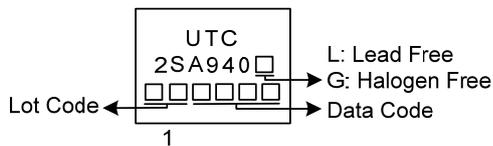
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SA940L- TA3-T	2SA940G-TA3-T	TO-220	B	C	E	Tube

Note: Pin Assignment: B: Base C: Collector E: Emitter

<p>2SA940G-TA3-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube (2) TA3: TO-220 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector- Base Voltage	V_{CBO}	-150	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Best Current	I_B	-0.5	A
Collector Current Continuous	I_C	-1.5	A
Collector Current Peak	I_{CM}	-3.0	A
Collector Dissipation	P_C	25	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction-to-Case	θ_{JC}	5.0	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -1.0\text{mA}, I_B = 0$	-150			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -5.0\text{mA}, I_B = 0$	-150			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_B = -1.0\text{mA}, I_C = 0$	-5.0			V
Collect Cut-off Current	I_{CBO}	$V_{CB} = -120\text{V}, I_E = 0$			-10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5.0\text{V}, I_C = 0$			-10	μA
ON CHARACTERISTICS						
DC Current Ratio	h_{FE}	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}$	40		140	
Base-Emitter on Voltage	$V_{BE(ON)}$	$V_{CE} = -5.0\text{V}, I_C = -500\text{mA}$	-0.65		-0.85	V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -0.5\text{A}, I_B = -50\text{mA}$			-1.5	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}, f = 1\text{MHz}$	4.0			MHz

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